## UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

PATENT NO.

: 6,936,897 B2

Page 1 of 1

**APPLICATION NO. : 09/259145** 

**DATED** 

: August 30, 2005

INVENTOR(S)

: Pai-Hung Pan and Nanseng Jeng

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the title page:

In Item (54) TITLE

change "INTERMEDIATE STRUCTURE HAVING A SILICON BARRIER LAYER **ENCAPSULATING A SEMICONDUCTOR** SUBSTRATE" to --INTERMEDIATE STRUCTURE HAVING A SILICON **NITRIDE BARRIER LAYER** 

**ENCAPSULATING A SEMICONDUCTOR** 

SUBSTRATE--

In ITEM (57) ABSTRACT, 12th line,

change "unmasked potion" to --unmasked

portions--

In the specification:

COLUMN 1, LINE 2,

change "SILICON BARRIER LAYER" to --SILICON NITRIDE BARRIER LAYER--

COLUMN 1, LINE 38,

change "layer 210 maybe" to --layer 210 may

COLUMN 2, LINE 24,

change "(see U.S. Pat." to --(see U.S. Pat.--

In the claims:

CLAIM 9, COLUMN 7, LINE 28,

change "first substrate" to --first surface--

Signed and Sealed this

Eighteenth Day of December, 2007

JON W. DUDAS Director of the United States Patent and Trademark Office